	Application No.	Applicant(s)	(M)
Notice of Allowability	10/791,870	OZAWA, YOSHIO	
	Examiner	Art Unit	······································
	Tu-Tu Ho	2818	
The MAILING DATE of this communication appears All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIOF of the Office or upon petition by the applicant. See 37 CFR 1.313	ears on the cover sheet wi (OR REMAINS) CLOSED in or other appropriate commit IGHTS. This application is so and MPEP 1308.	th the correspondence address on this application. If not included unication will be mailed in due cou	rse. THIS
1. This communication is responsive to <u>Amendment filed 09/2</u>	<u>23/2005</u> .		
2. The allowed claim(s) is/are <u>1,3-10 and 20</u> .			
3. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 4. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give 5. CORRECTED DRAWINGS (as "replacement sheets") must	e been received. e been received in Application cuments have been receive of this communication to file MENT of this application. itted. Note the attached EX es reason(s) why the oath o	on No d in this national stage application a reply complying with the require AMINER'S AMENDMENT or NOTI r declaration is deficient.	ements
(a) including changes required by the Notice of Draftspers		w (PTO-948) attached	
1) 🗌 hereto or 2) 🗍 to Paper No./Mail Date			
(b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the state of the sheet.	.84(c)) should be written on t	he drawings in the front (not the bac	ck) of
 DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT 	SIT OF BIOLOGICAL MATE FOR THE DEPOSIT OF BIO	ERIAL must be submitted. Note DLOGICAL MATERIAL.	e the
Attachment(s) 1. ☐ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview S Paper No. 98), 7. ☒ Examiner's	formal Patent Application (PTO-19) ummary (PTO-413), /Mail Date Amendment/Comment Statement of Reasons for Allowar Tu-Tu Ho October 1	nce

Application/Control Number: 10/791,870 Page 2

Art Unit: 2818

DETAILED ACTION

1. Applicant's Amendment filed 09/23/2005 has been reviewed and placed of record in the file.

EXAMINER'S AMENDMENT

- 2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.
- 3. This application is in condition for allowance except for the presence of claims 12-19 non-elected without traverse. Accordingly, claims 12-19 have been cancelled.

Allowable Subject Matter

4. Claims 1, 3-10, and 20 are allowable over the prior art of record.

The following is an examiner's statement of reasons for allowance: The prior art of record fails to teach or render obvious a nonvolatile semiconductor memory cell with all exclusive limitations as recited in claims 1 and 20, comprising a substrate; a stacked-gate structure stacked on the semiconductor substrate; and gate side-wall insulation films formed on both side surfaces of the stacked-gate structure; the stacked-gate structure comprising a tunnel insulation film, a floating gate electrode, an inter-electrode insulation film and a control gate electrode; a thickness

Page 3

of the gate side-wall insulation film increases, at a side portion of the floating gate electrode, from the inter-electrode insulation film side toward the tunnel insulation film side, and the width of the floating gate electrode in a channel length direction decreases from the inter-electrode insulation film side toward the tunnel insulation film side; a width (Q) of the floating gate electrode in the channel length direction being 50 nm or less on a surface of the tunnel insulation film, a distance (S) between distal ends of the gate side-wall insulation films being 1.3 or more times as great as the width of the floating gate electrode in the channel length direction; a portion of the floating gate contacting the inter-electrode insulation film; and a length (P) of said portion of the floating gate satisfying the relationship Q < P < S.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the 5. examiner should be directed to Tu-Tu Ho whose telephone number is (571) 272-1778. The examiner can normally be reached on 6:30 am - 5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, DAVID NELMS can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-8300.

Application/Control Number: 10/791,870

Art Unit: 2818

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Page 4

October 10, 2005